

1. Ionization Sensitization of Doping in Co-Deposited Organic Semiconductor Films

We have developed the *pn*-control technique by impurity doping for co-deposited films¹⁾ such as C₆₀:H₂Pc (fullerene: metal-free phthalocyanine) since a key element for exciton dissociation in organic solar cells is having a co-deposited films. During the course of these studies, we made accurate estimates of the carrier concentrations generated by impurity doping by means of Kelvin band-mapping,²⁾ from which we found evidence of higher doping efficiencies for co-deposited films compared to those for the respective single films.

Figure 3 shows the dependence of the doping efficiency on the doping concentration for C₆₀:H₂Pc and their component films. The doping efficiency is defined by the ratio of the carrier concentration created to the molecular concentration of Cs₂CO₃. The doping efficiencies of single films of C₆₀ and H₂Pc are around 10%. In contrast, those of the co-deposited films of C₆₀:H₂Pc are around 50%. Thus, we conclude that the doping efficiency was significantly enhanced in the co-deposited films.

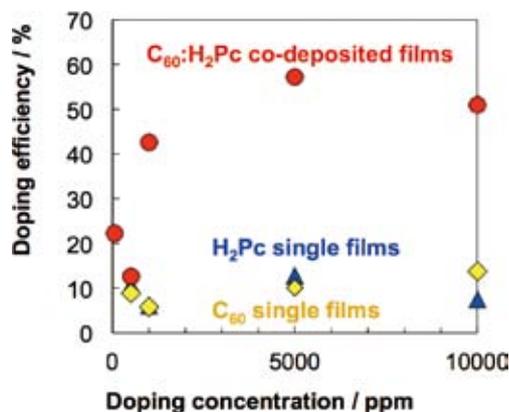


Figure 2. Dependence of doping efficiency on Cs₂CO₃ doping concentration for C₆₀:H₂Pc co-deposited films and their component films.

By making contact with C₆₀, since the electron transfer from the conduction band of H₂Pc to that of C₆₀ (Figure 4(a), blue arrow) occurs accompanied with energetic relaxation (0.7 eV), the electron concentration in H₂Pc decreases. Due to the shift in equilibrium, the electrons liberated from the donor levels accelerate, *i.e.*, the ionization rate (doping efficiency) for donors increases only in the H₂Pc region. Figure 4(b) shows the cross sectional energy structures of charge separating H₂Pc/C₆₀ superlattice after contact. In this model, the H₂Pc regions act as electron supplying layers to the C₆₀ regions. The C₆₀ regions act as electron transporting highways. Based on this model, we expected that the total ionization rate in H₂Pc:C₆₀ co-deposited films would increase further by increasing the H₂Pc ratio and obtained the ionization rate of 97% at a H₂Pc:C₆₀ ratio of 99:1.

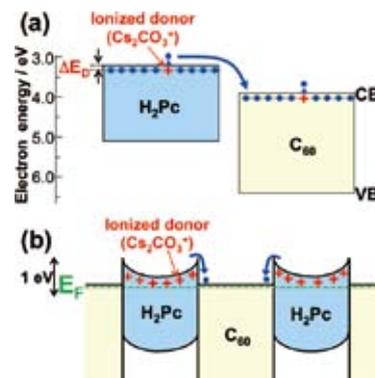


Figure 3. (a) Energy diagrams of Cs₂CO₃-doped H₂Pc and C₆₀ single films before contact. CB, VB, and ΔE_D denote the conduction band, the valence band, and the activation energy of the donors, respectively. (b) Cross sectional energy structure of a Cs₂CO₃-doped H₂Pc/C₆₀ superlattice model after contact.

2. Mapping of Band-Bending for Organic *pn*-Homojunctions

A precise band-mapping for organic *pn*-homojunctions, which have various balance of doping concentration between *p*- and *n*-type layers, was performed by measuring the film thickness dependence of the work function from both sides of the *pn*-homojunction interface using a Kelvin probe. Band-bending including the simultaneous development of depletion layer in underlying *n*-type layer induced by the deposition of *p*-type layer, and vice versa, should be taken into account for the precise fitting based on the Poisson equation. Validity of the conventional theory of space charge layer suggests that the dopants are spatially fixed even in the organic semiconductor films. The present result allows the precise design of the built-in potential in the organic solar cells.

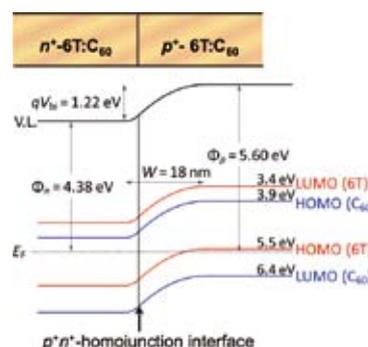


Figure 4. Energy band diagram of the *p*⁺*n*⁺-homojunction. VL, E_F , VB, and CB denote the vacuum level, Fermi level, the valence band and the conduction band, respectively.

References

- 1) M. Kubo, T. Kaji and M. Hiramoto, *Appl. Phys. Lett.* **103**, 263303 (2013).
- 2) Y. Shinmura, N. Ishiyama, T. Kaji and M. Hiramoto, *Appl. Phys. Express* **7**, 071601 (2014).